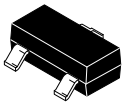
Silicon Hot-Carrier Diodes

Schottky Barrier Diodes

MBD701, MMBD701L, SMMBD701L

TO−92 2−Lead
CASE 182
STYLE 1

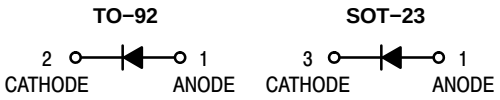


SOT−23 (TO−236)
CASE 318
STYLE 8

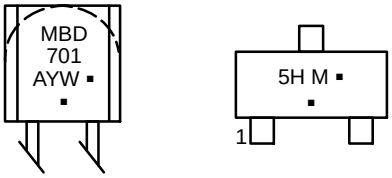
These devices are designed primarily for high−efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low−cost, high−volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

Features

- Extremely Low Minority Carrier Lifetime − 15 ps (Typ)
- Very Low Capacitance − 1.0 pF @ V_R = 20 V
- High Reverse Voltage − to 70 V
- Low Reverse Leakage − 200 nA (Max)
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant



MARKING DIAGRAMS



TO−92 SOT−23

A = Assembly Location
Y = Year
W = Work Week
5H = Device Code (SOT−23)
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	V
Forward Power Dissipation @ T_A = 25°C MBD701 MMBD701L, SMMBD701L Derate above 25°C MBD701 MMBD701L, SMMBD701L	P_F	 280 200 2.8 2.0	mW mW/°C
Operating Junction Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)R}$	70	–	–	V
Total Capacitance (V_R = 20 V, f = 1.0 MHz) Figure 1	C_T	–	0.5	1.0	pF
Reverse Leakage (V_R = 35 V) Figure 3	I_R	–	9.0	200	nAdc
Forward Voltage (I_F = 1.0 mAdc) Figure 4	V_F	–	0.42	0.5	Vdc
Forward Voltage (I_F = 10 mAdc) Figure 4	V_F	–	0.7	1.0	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping†
MMBD701LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SMMBD701LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel

DISCONTINUED (Note 1)

MBD701G	TO−92 (Pb−Free)	1,000 Units / Bulk
MMBD701LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

Share Feedback
Your Opinion Matters

TYPICAL ELECTRICAL CHARACTERISTICS

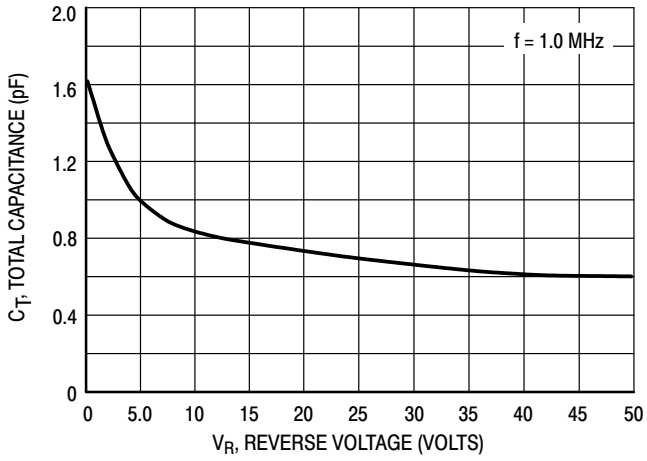

Figure 1. Total Capacitance

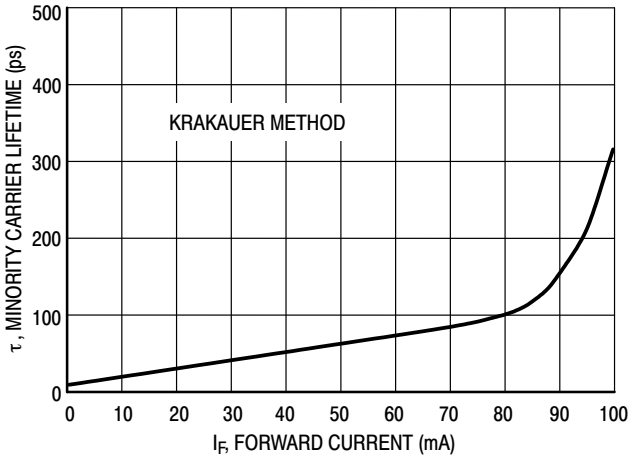

Figure 2. Minority Carrier Lifetime

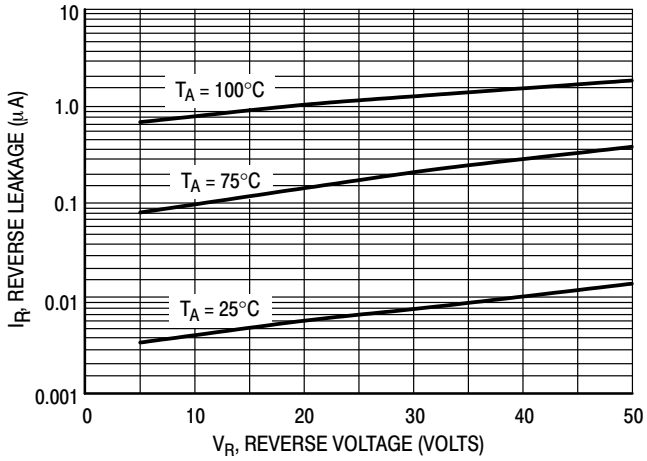

Figure 3. Reverse Leakage

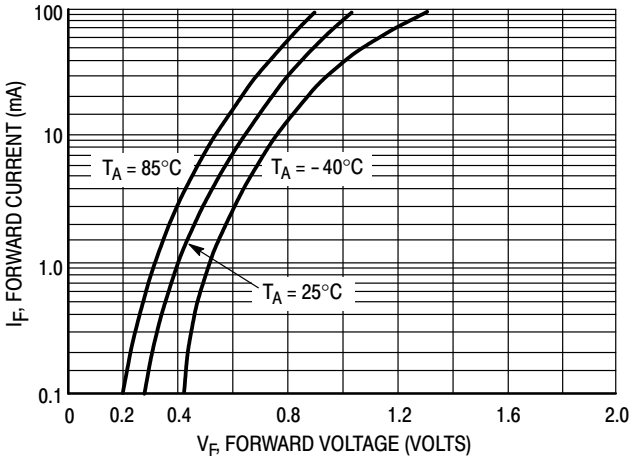

Figure 4. Forward Voltage

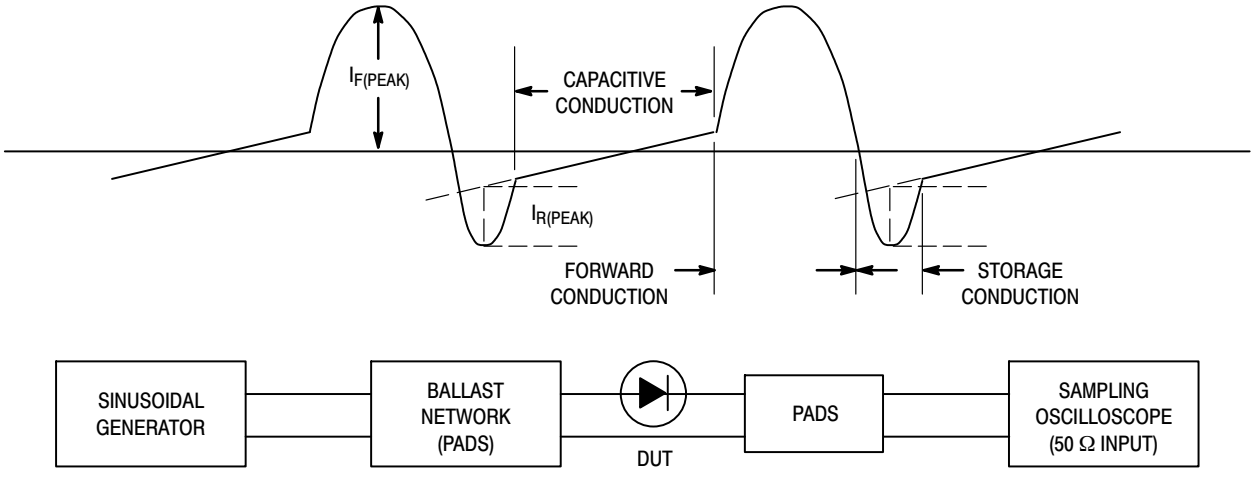

Figure 5. Krakauer Method of Measuring Lifetime

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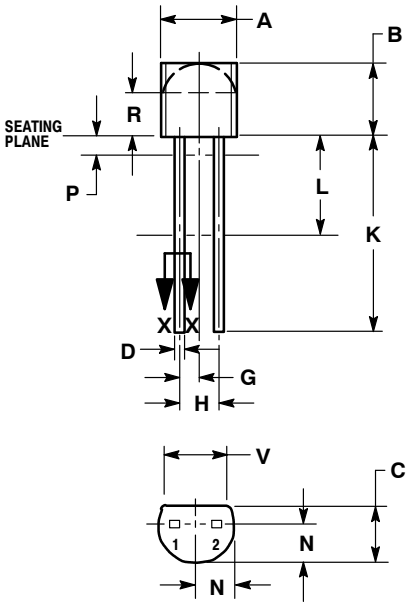
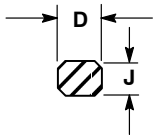
TO−92 (TO−226)
CASE 182−06
ISSUE L

DATE 04/18/1998

SCALE 1:1





SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.050 BSC		1.27 BSC	
H	0.100 BSC		2.54 BSC	
J	0.014	0.016	0.36	0.41
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.03	2.66
P	---	0.050	---	1.27
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:
PIN 1. ANODE
2. CATHODE

STYLE 2:
PIN 1. CATHODE
2. ANODE

STYLE 3:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2

STYLE 4:
CANCELLED

STYLE 5:
PIN 1. INPUT
2. OUTPUT

DOCUMENT NUMBER:	**98ASB42118B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**TO−92 (TO−226)**		**PAGE 1 OF 1**

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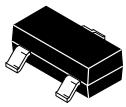
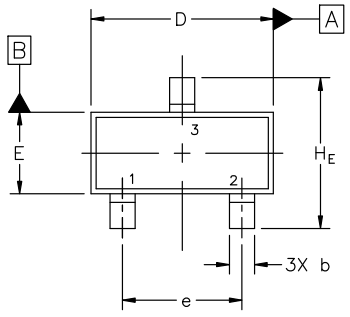


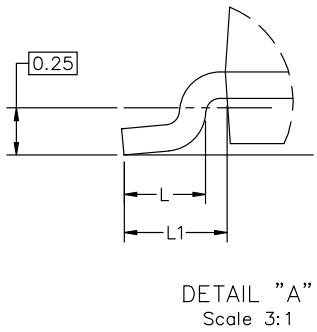
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

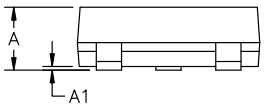
DATE 14 AUG 2024



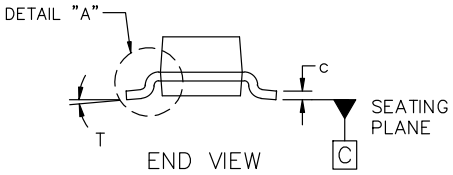
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

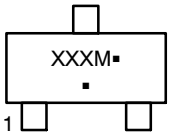


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

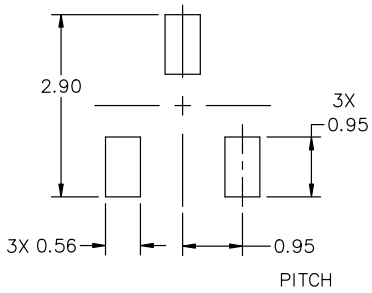
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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